



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Teruo TAKIZAWA et al.

Application No.: 09/763,365

Filed: February 23, 2001

Group Art Unit: 2813

Examiner: D. Hogans

Docket No.: 108680

For: SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF

AMENDMENT UNDER 37 C.F.R. §1.111

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed February 21, 2002, the period for response being extended by the attached Petition for Extension of Time, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 7 as follows:

1. (Amended) A semiconductor device, comprising:

a metal-oxide-semiconductor field-effect transistor that includes:

a gate insulation film and a gate electrode on the gate insulation film,

the gate electrode including a germanium film on the gate insulation film.

7. (Amended) A semiconductor device, comprising:

an n-channel metal-oxide-semiconductor field-effect transistor; and

a p-channel metal-oxide-semiconductor field-effect transistor,

at least one of the n-channel metal-oxide-semiconductor field-effect transistor

and the p-channel metal-oxide-semiconductor field-effect transistor including:

a gate insulation film and a gate electrode on the gate insulation film,

the gate electrode including a germanium film on the gate insulation film.

Please add new claims 15 and 16 as follows:

--15. The semiconductor device according to claim 1, further including a silicon

substrate, the metal-oxide-semiconductor field-effect transistor being formed on the silicon substrate.--